

March 1997

High-Reliability CMOS 256-Word x 4-Bit LSI Static RAM

Features

- For Applications in Aerospace, Military, and Critical Industrial Equipment
- Interfaces Directly with CDP1802 Microprocessor
- Very Low Operating Current
 - At $V_{DD} = 5V$ and Cycle Time = $1\mu s$ 4mA (Typ)
- Static CMOS Silicon-On-Sapphire Circuitry
 - CD4000 Series Compatible
- Industry Standard Pinout
- Two Chip Select Inputs - Simple Memory Expansion
- Memory Retention for Standby. 2V (Min) Battery Voltage
- Single Power Supply Operation 4V to 6.5V
- High Noise Immunity 30% of V_{DD} 4V to 6.5V
- Output Disable for Common I/O Systems
- Three-State Data Output for Bus Oriented Systems
- Separate Data Inputs and Outputs
- Latch-Up-Free Transient Radiation Tolerance

Description

The CDP1822C/3 is a 256 word by 4-bit random access memory designed for use in memory systems where high speed, low operating current, and simplicity in use are desirable. The CDP1822 features high speed and excellent noise immunity. It has separate data inputs and outputs and utilizes a single power supply of 4V to 6.5V.

Two Chip Select inputs simplify system expansion. An output Disable control provides Wire-OR-capability and is also useful in common Input/Output systems. The Output Disable input allows this RAM to be used in common data Input/Output systems by forcing the output into a high impedance state during a write operation independent of the Chip Select input condition. The output assumes a high impedance state when the Output Disable is at high level or when the chip is deselected by CS_1 and/or CS_2 .

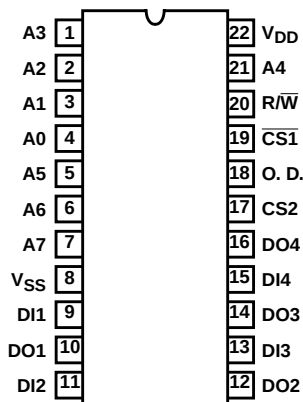
The high noise immunity of the CMOS technology is preserved in this design. For TTL interfacing at 5V operation, excellent system noise margin is preserved by using an external pull-up resistor at each input.

Ordering Information

PACKAGE	TEMP. RANGE	PART NUMBER	PKG. NO.
SBDIP	-55°C to +125°C	CDP1822CD3	D22.4A

Pinout

CDP1822C/3 (SBDIP)
TOP VIEW



OPERATIONAL MODES

MODE	INPUTS				OUTPUT
	CHIP SELECT 1 ($\overline{CS_1}$)	CHIP SELECT 2 ($\overline{CS_2}$)	OUTPUT DISABLE ($\overline{OD}$)	READ/ WRITE ($\overline{R/W}$)	
Read	0	1	0	1	Read
Write	0	1	0	0	Data In
Write	0	1	1	0	High Impedance
Standby	1	X	X	X	High Impedance
Standby	X	0	X	X	High Impedance
Output Disable	X	X	1	X	High Impedance

Logic 1 = High, Logic 0 = Low, X = Don't Care

CDP1822C/3

Absolute Maximum Ratings

DC Supply Voltage Range, (V_{DD})
 (All Voltages Referenced to V_{SS} Terminal)
 CDP1822C/3 -0.5V to +7V
 Input Voltage Range, All Inputs -0.5V to V_{DD} +0.5V
 Operating Temperature Range (T_A) -55°C to +125°C

Thermal Information

Thermal Resistance (Typical)
 SBDIP Package 80 $^{\circ}\text{C/W}$ 21 $^{\circ}\text{C/W}$
 Maximum Storage Temperature Range (T_{STG}) ... -65°C to +150°C
 Maximum Lead Temperature (During Soldering) +265°C
 Maximum Junction Temperature +150°C

Recommended Operating Conditions

At T_A = Full Package Temperature Range. For maximum reliability, operating conditions should be selected so that operation is always within the following ranges:

PARAMETER	LIMITS		UNITS
	MIN	MAX	
DC Operating Voltage Range	4	6.5	V
Input Voltage Range	V_{SS}	V_{DD}	V

Static Electrical Specifications

PARAMETER	SYMBOL	CONDITIONS			LIMITS				UNITS
		V _O (V)	V _{IN} (V)	V _{DD} (V)	-55°C, +25°C		+125°C		
					MIN	MAX	MIN	MAX	
Quiescent Device Current (Note 1)	I _{DD}	-	0, 5	5	-	390	-	1000	μA
Output Low (Sink) Current (Note 1)	I _{OL}	0.4	0, 5	5	2.6	-	1.6	-	mA
Output High (Source) Current (Note 1)	I _{OH}	4.6	0, 5	5	-	-1.2	-	-0.8	mA
Output Voltage Low-Level	V _{OL}	-	0, 5	5	-	0.1	-	0.5	V
Output Voltage High-Level	V _{OH}	-	0, 5	5	V _{DD} - 0.1	-	V _{DD} - 0.5	-	V
Input Low Voltage	V _{IL}	0.5, 4.5	-	5	-	0.3 V _{DD}	-	0.3 V _{DD}	V
Input High Voltage	V _{IH}	0.5, 4.5	-	5	0.7 V _{DD}	-	0.7 V _{DD}	-	V
Input Leakage Current (Note 1)	I _{IN}	-	0, 5	5	-	±3.2	-	±10	μA
Operating Current (Note 1)	I _{DD1}	-	0, 5	5	-	6.5	-	10	mA
Three-State Output Leakage Current	I _{OUT}	0, 5	0, 5	5	-	±3.2	-	± 19	μA
Input Capacitance	C _{IN}	-	-	-	-	7.5	-	7.5	pF
Output Capacitance	C _{OUT}	-	-	-	-	7.5	-	7.5	pF

NOTE:

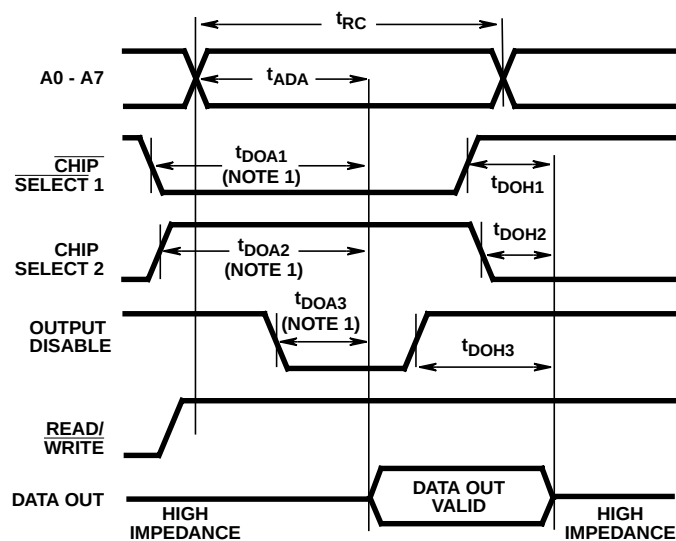
- Limits designate 100% testing, all other limits are designer's parameters under given test conditions and do not represent 100% testing.

Read Cycle Dynamic Electrical Specifications $t_R, t_F = 10\text{ns}, C_L = 50\text{pF}$

PARAMETER	SYMBOL	V _{DD} (V)	LIMITS				UNITS
			+25°C, -55°C		+125°C		
			MIN	MAX	MIN	MAX	
Read Cycle (Note 1)	t _{RC}	5	370	-	500	-	ns
Access from Address (Note 1)	t _{ADA}	5	-	370	-	500	ns
Output Valid from $\overline{\text{Chip Select 1}}$ (Note 1)	t _{DOA1}	5	-	370	-	500	ns
Output Valid from Chip Select 2 (Note 1)	t _{DOA2}	5	-	370	-	500	ns
Output Active from Output Disable (Note 1)	t _{DOA3}	5	-	170	-	225	ns
Output Hold from $\overline{\text{Chip Select 1}}$	t _{DOH1}	5	10	-	20	-	ns
Output Hold from Chip Select 2	t _{DOH2}	5	10	-	20	-	ns
Output Hold from Output Disable	t _{DOH3}	5	10	-	20	-	ns

NOTE:

1. Limits designate 100% testing. All other limits are designer's parameters under given test conditions and do not represent 100% testing



NOTE: Minimum timing for valid data output. Longer times will initiate an earlier but invalid output.

FIGURE 1. READ CYCLE WAVEFORMS AND TIMING DIAGRAM

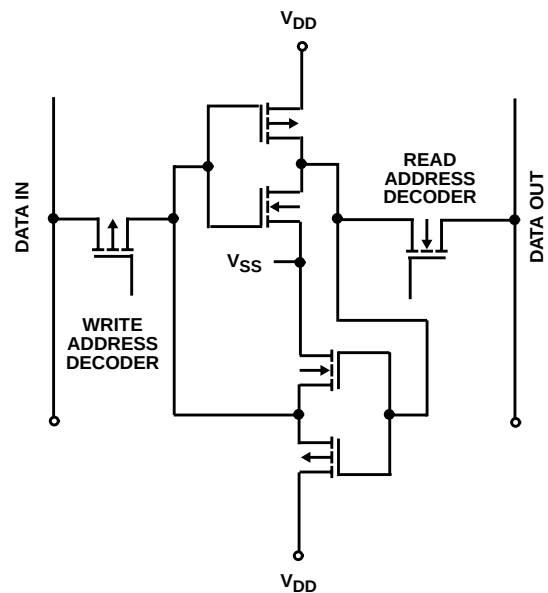


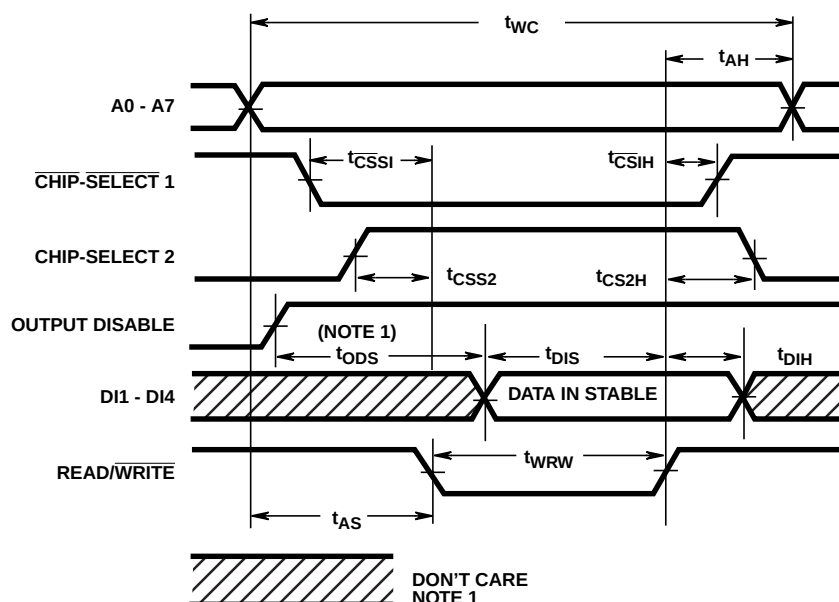
FIGURE 2. MEMORY CELL CONFIGURATION

Write Cycle Dynamic Electrical Specifications $t_R, t_F = 10\text{ns}$, $C_L = 50\text{pF}$

PARAMETER	SYMBOL	V _{DD} (V)	LIMITS				UNITS
			+25°C, -55°C		+125°C		
			MIN	MAX	MIN	MAX	
Write Cycle (Note 1)	t _{WC}	5	400	-	560	-	ns
Address Setup (Note 1)	t _{AS}	5	160	-	225	-	ns
Address Hold (Note 1)	t _{AH}	5	40	-	55	-	ns
Write Pulse Width (Note 1)	t _{WRW}	5	200	-	280	-	ns
Data in Setup (Note 1)	t _{DIS}	5	200	-	280	-	ns
Data in Hold (Note 1)	t _{DIH}	5	40	-	55	-	ns
Chip Select 1 Setup	t _{CSS1}	5	200	-	280	-	ns
Chip Select 2 Setup	t _{CSS2}	5	200	-	280	-	ns
Output Disable Setup	t _{ODS}	5	140	-	225	-	ns

NOTE:

- Limits designate 100% testing. All other limits are designer's parameters under given test conditions and do not represent 100% testing



NOTE:

- t_{ODS} is required for common I/O operation only; for separate I/O operations, output disable is don't care.

FIGURE 3. WRITE CYCLE TIMING WAVEFORMS

Data Retention Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		LIMITS				UNITS
		V _{DR} (V)	V _{DD} (V)	+25°C, -55°C		+125°C		
				MIN	MAX	MIN	MAX	
Minimum Data Retention Voltage (Note 1)	V _{DR}	-	-	-	2	-	2.5	V
Data Retention Quiescent Current (Note 1)	I _{DD}	2	-	-	70	-	380	μA
Chip Deselect to Data Retention Time	t _{CDR}	-	5	450	-	650	-	ns
		-	10					
Recovery to Normal Operation Time	t _{RC}	5	5	450	-	650	-	ns

NOTE:

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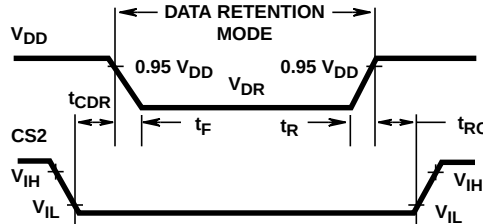
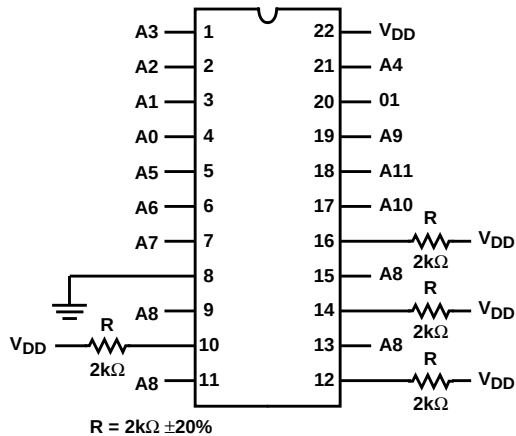
FIGURE 4. LOW V_{DD} DATA RETENTION TIMING WAVEFORMS

FIGURE 5. DYNAMIC/OPERATING BURN-IN CIRCUIT AND TIMING DIAGRAM

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